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[DMP6023LFG-13](#)

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**DMP6023LFG**

**60V P-CHANNEL ENHANCEMENT MODE MOSFET  
POWERDI®**

### Product Summary

$V_{(BR)DSS}$	$R_{DS(ON) \max}$	$I_D \max$ $T_A = +25^\circ\text{C}$
-60V	25mΩ @ $V_{GS} = -10\text{V}$	-7.7A
	33mΩ @ $V_{GS} = -4.5\text{V}$	-6.8A

### Features and Benefits

- Low  $R_{DS(ON)}$  – ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

### Description and Applications

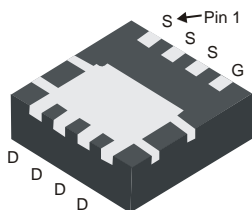
This MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

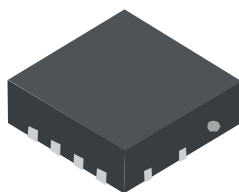
### Mechanical Data

- Case: POWERDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208(63)
- Weight: 0.072 grams (Approximate)

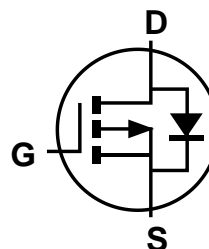
POWERDI3333-8



Bottom View



Top View



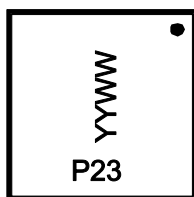
Equivalent Circuit

### Ordering Information (Note 4)

Part Number	Case	Packaging
DMP6023LFG-7	POWERDI3333-8	2,000/Tape & Reel
DMP6023LFG-13	POWERDI3333-8	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

### Marking Information



P23= Product Type Marking Code  
YYWW = Date Code Marking  
YY = Last Digit of Year (ex: 13 = 2013)  
WW = Week Code (01 ~ 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-60	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-7.7 -6.2	A
	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-10.3 -8.2	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I <sub>DM</sub>	-55	A
Maximum Continuous Body Diode Forward Current (Note 6)			I <sub>S</sub>	-2.2	A
Avalanche Current, L = 0.1mH			I <sub>AS</sub>	-35.5	A
Avalanche Energy, L = 0.1mH			E <sub>AS</sub>	62.9	mJ

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Total Power Dissipation (Note 5)			P <sub>D</sub>	1.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R <sub>θJA</sub>	123	°C/W
	t < 10s			69	
Total Power Dissipation (Note 6)			P <sub>D</sub>	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R <sub>θJA</sub>	60	°C/W
	t < 10s			34	
Thermal Resistance, Junction to Case (Note 6)			R <sub>θJC</sub>	6.3	
Operating and Storage Temperature Range			T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-1	µA	V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1	—	-3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	—	25	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -5A
		—	—	33		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -4A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	2569	—	pF	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	179	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	143	—	pF	
Gate Resistance	R <sub>g</sub>	—	8	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>g</sub>	—	26.5	—	nC	V <sub>DS</sub> = -30V, I <sub>D</sub> = -5A
Total Gate Charge (V <sub>GS</sub> = -10V)	Q <sub>g</sub>	—	53.1	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	7.1	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	12.6	—	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	—	6	—	ns	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -30V, R <sub>G</sub> = 3Ω, I <sub>D</sub> = -5A
Turn-On Rise Time	t <sub>r</sub>	—	7.1	—	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	—	110	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	62	—	ns	
Body Diode Reverse Recovery Time	t <sub>rr</sub>	—	20	—	ns	I <sub>F</sub> = -5A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	—	14	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.



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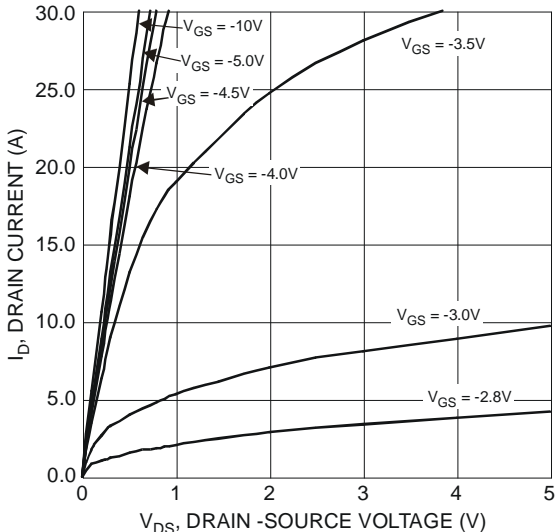


Figure 1 Typical Output Characteristics

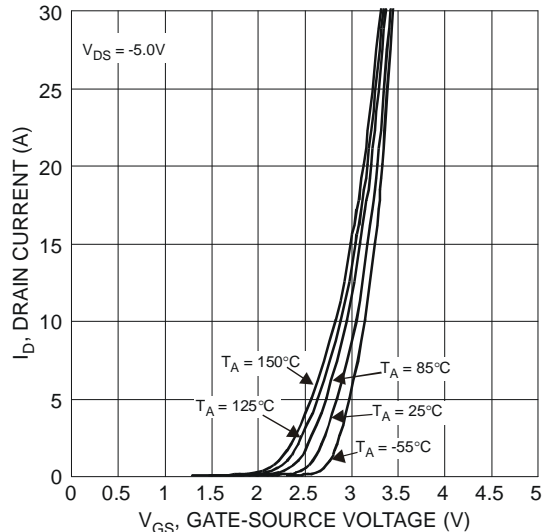


Figure 2 Typical Transfer Characteristics

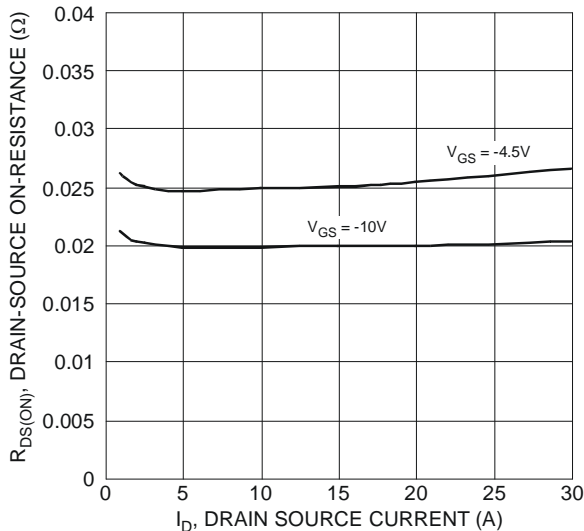


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

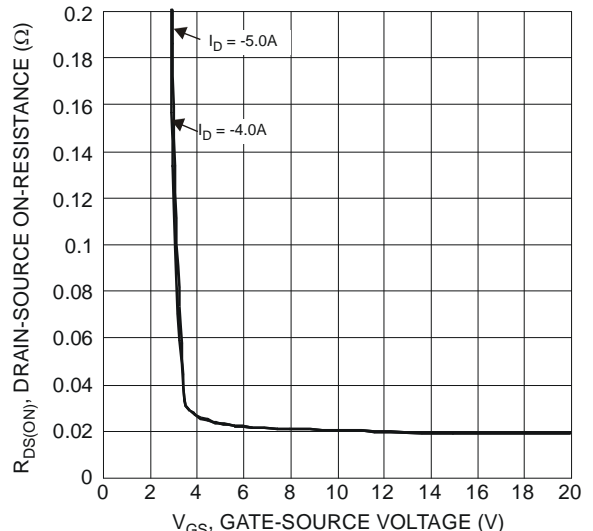


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

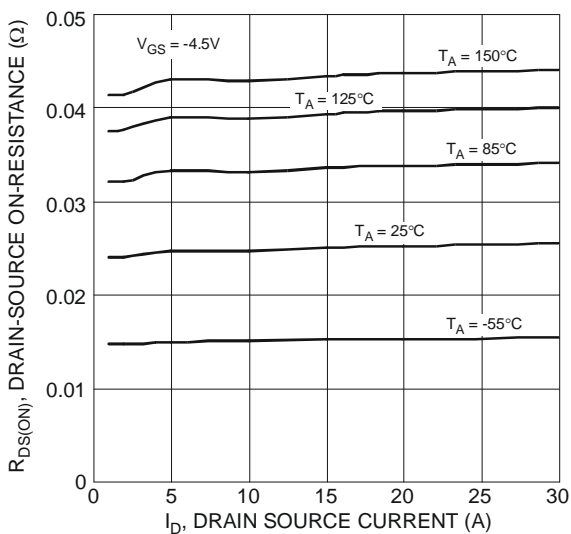


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

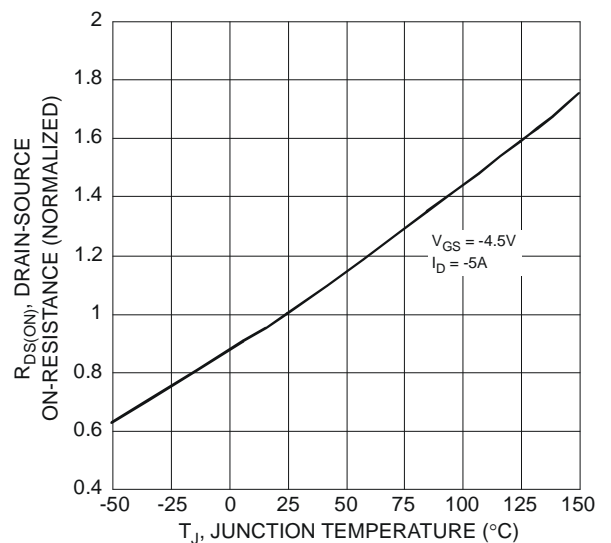


Figure 6 On-Resistance Variation with Temperature



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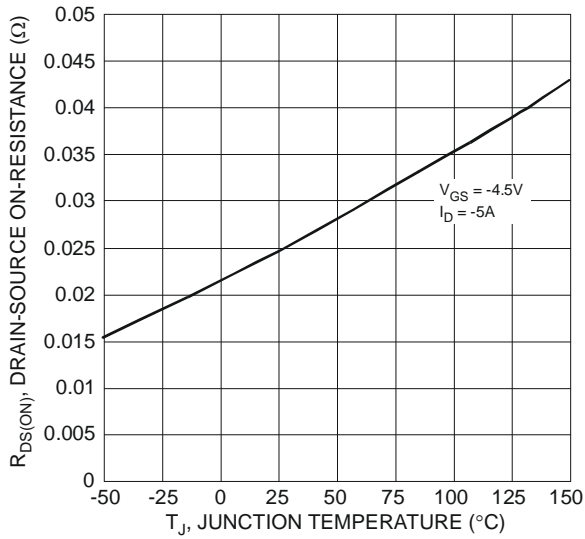


Figure 7 On-Resistance Variation with Temperature

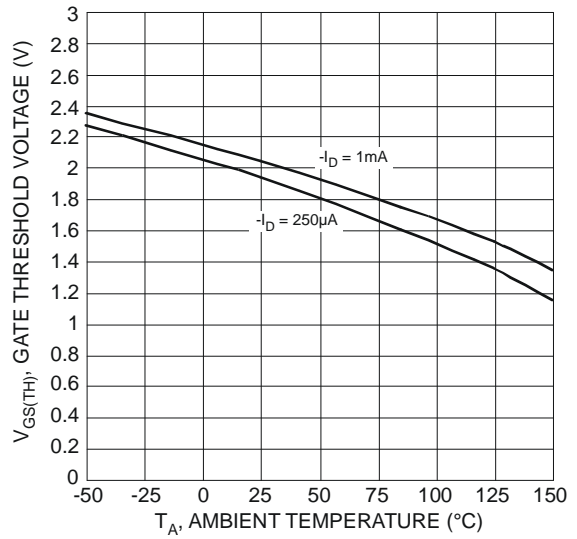


Figure 8 Gate Threshold Variation vs. Ambient Temperature

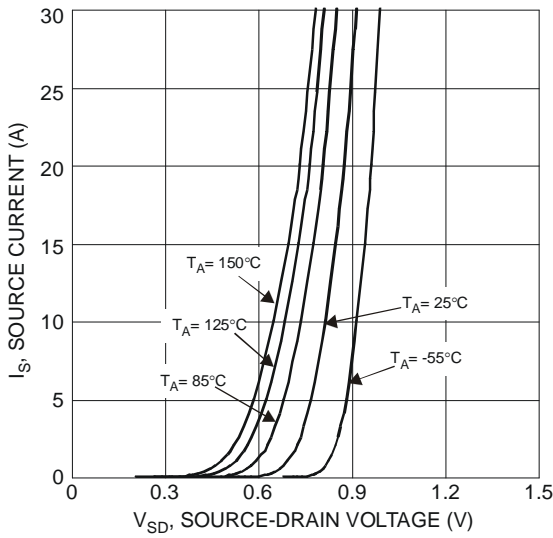


Figure 9 Diode Forward Voltage vs. Current

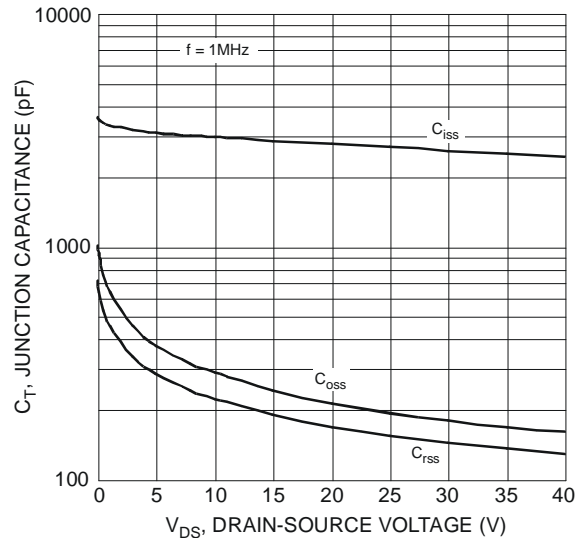


Figure 10 Typical Junction Capacitance

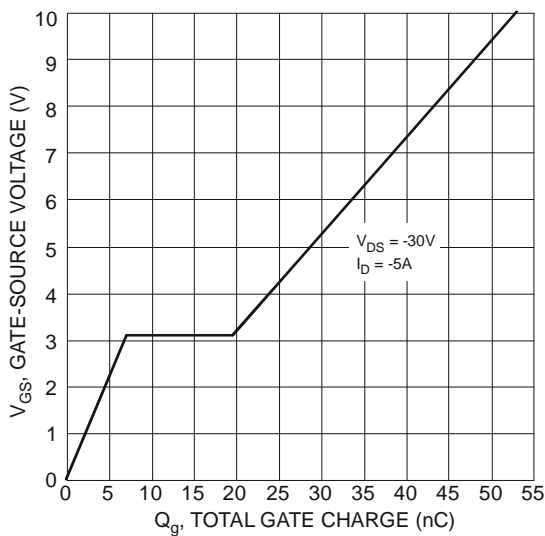


Figure 11 Gate-Charge Characteristics

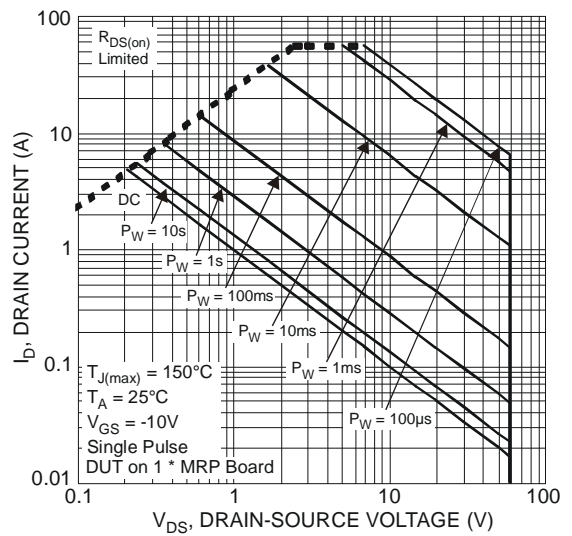


Figure 12 SOA, Safe Operation Area



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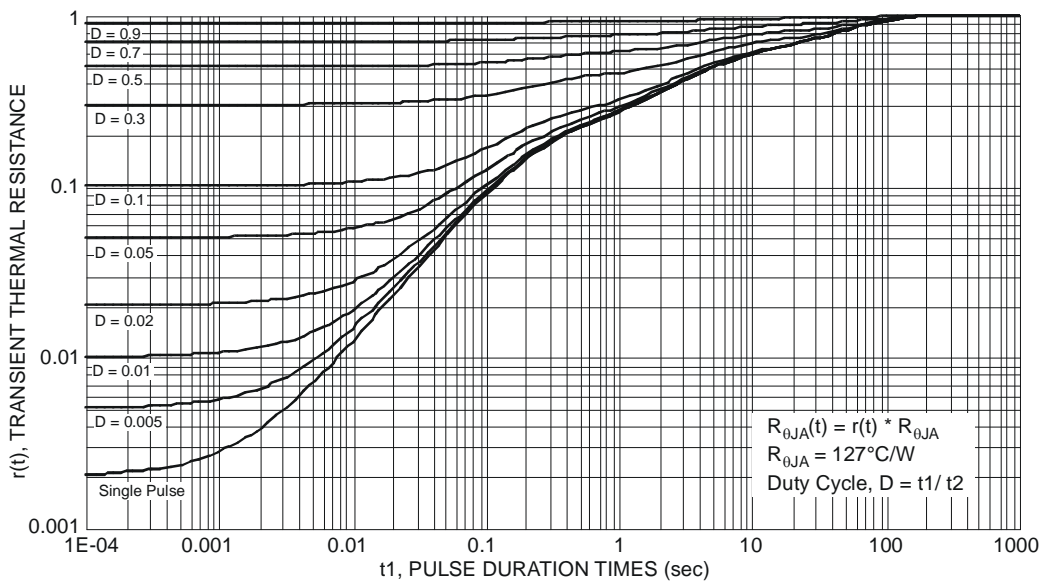
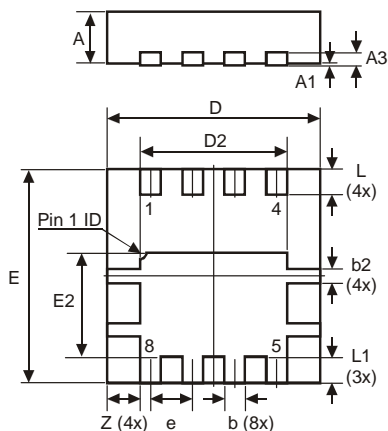


Figure 13 Transient Thermal Resistance

### Package Outline Dimensions

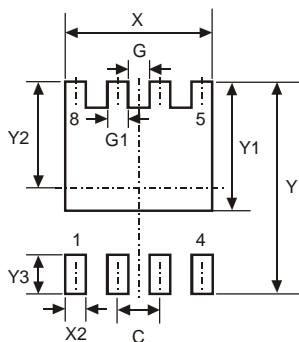
Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



POWERDI <sup>®</sup> 3333-8			
Dim	Min	Max	Typ
D	3.25	3.35	3.30
E	3.25	3.35	3.30
D2	2.22	2.32	2.27
E2	1.56	1.66	1.61
A	0.75	0.85	0.80
A1	0	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	-	-	0.20
L	0.35	0.45	0.40
L1	-	-	0.39
e	-	-	0.65
Z	-	-	0.515
All Dimensions in mm			

### Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.650
G	0.230
G1	0.420
Y	3.700
Y1	2.250
Y2	1.850
Y3	0.700
X	2.370
X2	0.420

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